

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(reducing near plasma near preclean\$3) same (wiring near level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:42
L2	281	((etch\$3 or pattern\$3 or remov\$3) same (recess or hole or open\$3)) same (wiring near level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:11
L3	76	2 same mask\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:12
L4	0	3 and (reduc\$3 near plasma near preclean\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:13
L5	37	3 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:13
L6	29	5 and @pd<"20030627"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:14
L7	1	(reducing near plasma near preclean\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:43
L8	1	(reducing near plasma near preclean\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:46
L9	2	"6261951".pn. and (reduc\$3 near plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:46

L10	2	"6255217".pn. and (reduc\$3 near plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:46
L11	5284	(reduc\$3 near plasma)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:51
L12	0	11 same (selective near etch\$3) same ( low near2 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:50
L13	0	11 and (selective near etch\$3) same ( low near2 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:48
L14	0	11 same (etch\$3 same (low near2 dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:49
L15	0	11 and (etch\$3 same (low near2 dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:49
L16	0	11 and (etch\$3 same (low near2 dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:49
L17	0	11 same (low near "k" near dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:50

L18	0	11 same ((selective near etch\$3) same dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 15:50
L19	42	(reduc\$3 near plasma) same damascene	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 16:28
L20	104	gambino-jeffrey-p.in.	US-PGPUB; USPAT	OR	OFF	2005/06/16 16:29
L21	1	20 and (reduc\$3 near plasma)	US-PGPUB; USPAT	OR	OFF	2005/06/16 16:30
L22	12	20 and (interconnect\$3 near structure)	US-PGPUB; USPAT	OR	OFF	2005/06/16 16:30
L23	4216	(etch\$3 same dielectric) same (reduc\$3 near plasma or hydrogen or nitrogen or ammonia)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 19:13
L24	695	23 same (trench or damascene)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 17:02
L25	380	24 and @pd<"20030627"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 17:03
L26	257	25 and mask\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 18:07
L27	97	26 and (hard near mask\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 18:08
L28	636	(etch\$3 same (low near "k" or silk or flare or parylene)) same (hydrogen or nitrogen or ammonia)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 19:15

L29	57	28 same (hard near mask\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 19:15
L30	26	29 and @pd<"20030627"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/16 19:16